

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

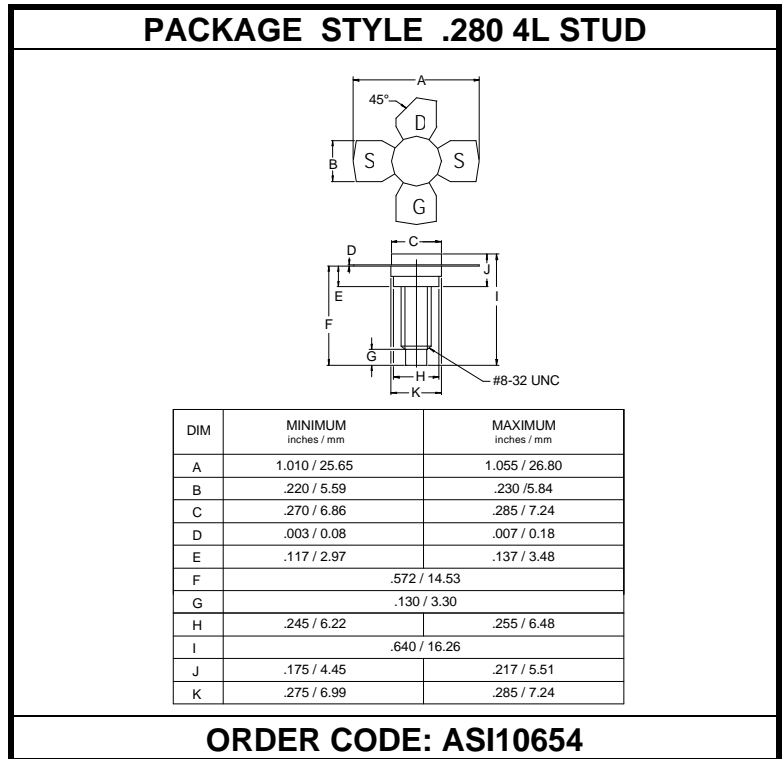
The ASI TVV005 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	55 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	50 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	3.5 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	30			V
BV_{CER}	$I_C = 20$ mA $R_{BE} = 10 \Omega$	55			V
BV_{CBO}	$I_C = 20$ mA	55			V
BV_{EBO}	$I_E = 2.0$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	10		---	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			35	pF
P_G	$V_{CE} = 28$ V $P_{OUT} = 5.0$ W $I_C = 1.0$ A $f = 225$ MHz	15			dB
IMD_1	$V_{CE} = 28$ V $P_{OUT} = 5.0$ W $I_C = 1.0$ A $f = 225$ MHz Vision Carrier = -8 dB ref. Sound Carrier = -7 dB ref. Sideband Signal = -16 dB ref.	-55			dBc
Ψ	$V_{CE} = 28$ V $P_{OUT} = 5.0$ W $I_C = 1.0$ A $f = 225$ MHz Load VSWR = ∞ :1, All Phase Angles	No Degradation in Output Power			